ANALOG DEVICES

Inverting High-Speed Operational Amplifier

OP-01

FEATURES

- **Fast Settling Time** ..... **1μs to 0.1% Max**
- **High Slew Rate** ..... **12V/μs Min**
- **Power Bandwidth** ..... **150kHz Min**
- **Low Power Consumption** ..... **90mW Max**
- **Excellent DC Specifications**
- **Internally Compensated**
- **Ideal DAC Output Amplifier**
- **MIL-STD-883 Processing Available**
- **Fits Standard 741 Sockets**
- **Low Cost**
- **Available in Die Form**

ORDERING INFORMATION†

T_A = 25°C V_{OS} MAX (mV)	PACKAGE TO-99	CERDIP 8-PIN	PLASTIC 8-PIN	OPERATING TEMPERATURE RANGE
0.7	OP01J*	—	—	MIL
0.7	—	—	OP01HP	COM
5.0	OP01GJ	—	—	MIL
5.0	OP01CJ	OP01CZ	OP01CP	COM

* For devices processed in total compliance to MIL-STD-883, add /883 after part number. Consult factory for 883 data sheet.

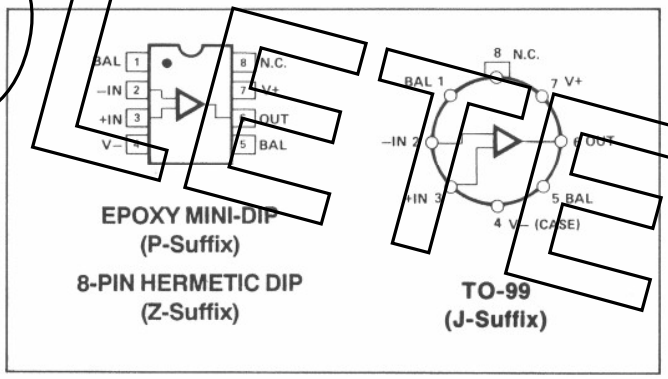
† Burn-in is available on commercial and industrial temperature range parts in CerDIP, plastic DIP, and TO-can packages.

GENERAL DESCRIPTION

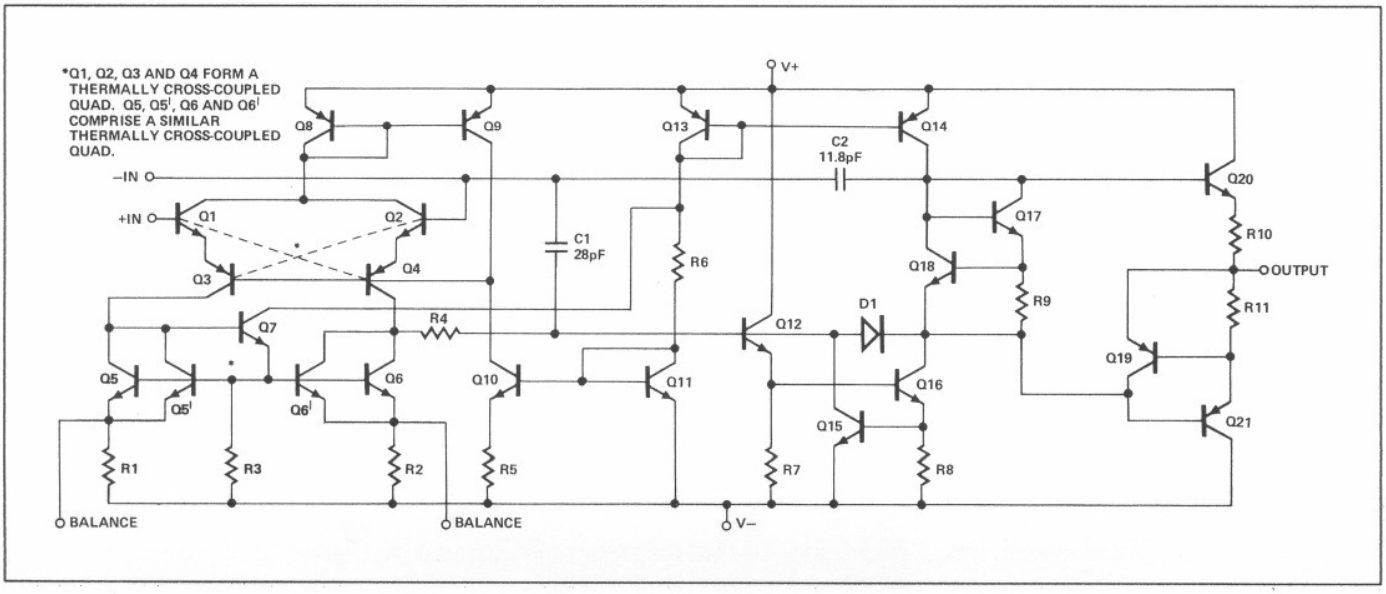
The OP-01 series of monolithic inverting high-speed operational amplifiers combines high slew rate, fast settling time and excellent DC input characteristics. An internal feedforward frequency compensation network provides simplicity of application — no external capacitors are required for stable, high-speed performance. The fast output response is achieved without sacrifice of input bias current or power consumption. A 250kHz typical power bandwidth is attained with a small-signal bandwidth of only 2.5MHz, thus board layout is non-critical. The OP-01 is completely protected at both input and output, fits standard 741 sockets, and is offset nulled with a 10kΩ potentiometer.

The fast output response combined with excellent settling time makes the OP-01 ideal for use as a D/A converter output amplifier.

PIN CONNECTIONS



SIMPLIFIED SCHEMATIC



OP-01

ABSOLUTE MAXIMUM RATINGS (Note 1)

Total Supply Voltage, OP-01,OP-01H, OP-01N, OP-01NT,
OP-01G, OP-01GT ..... ±22V
OP-01G, OP-01C, OP-01GR ..... ±20V
Differential Input Voltage ..... ±30V
Input Voltage (Note 2) ..... ±15V
Short-Circuit Duration ..... Indefinite
Operating Temperature Range
OP-01, OP-01G ..... –5°C to +125°C
OP-01H, OP-01C ..... 0°C to +70°C
Junction Temperature (T_J) ..... –65°C to +150C
Storage Temperature
J and Z Packages ..... –65°C to +150°C
P Packages ..... –65°C to +150°C
Lead Temperature (Soldering, 60 sec) ..... +300°C

PACKAGE TYPE	Θ_{JA} (NOTE 3)	Θ_{JC}	UNITS
TO-99 (J)	170	24	°C/W
8-Pin Hermetic DIP (Z)	162	26	°C/W
8-Pin Plastic DIP (P)	110	50	°C/W

NOTES:
1. Absolute maximum ratings apply to both DICE and packaged parts, unless otherwise noted.
2. For supply voltages less than ±15V, the maximum input voltage is the supply voltage.
3. Θ_{JA} is specified for worst case mounting conditions, i.e., Θ_{JA} is specified for device in socket for TO, CerDIP and P-DIP packages.

ELECTRICAL CHARACTERISTICS at $V_S = \pm 15V$, $T_A = 25°C$, unless otherwise noted.

PARAMETER	SYMBOL	CONDITIONS	OP-01 OP-01H MIN	OP-01 OP-01H TYP	OP-01 OP-01H MAX	OP-01G OP-01C MIN	OP-01G OP-01C TYP	OP-01G OP-01C MAX	UNITS
Input Offset Voltage	V_{OS}	$R_S \leq 20k\Omega$	—	0.3	0.7	—	2.0	5.0	mV
Input Offset Current	I_{OS}		—	0.5	2.0	—	2.0	20	nA
Input Bias Current	I_B		—	18	30	—	25	100	nA
Input Voltage Range	IVR		±12	±13	—	±12	±13	—	V
Common-Mode Rejection Ratio	CMRR	$V_{CM} = \pm 10V$ $R_S \leq 20k\Omega$	85	110	—	80	100	—	dB
Power Supply Rejection Ratio	PSRR	$V_S = \pm 5V$ to $\pm 20V$ $R_S \leq 20k\Omega$	—	10	60	—	100	150	μV/V
Output Voltage Swing	V_O	$R_L \geq 5k\Omega$ $R_L \geq 2k\Omega$	±12.5 ±12.0	±13.5 ±13.0	—	±12.5 ±12.0	±13.5 ±13.0	—	V
Large-Signal Voltage Gain	A_{VO}	$R_L \geq 2k\Omega$ $V_O = \pm 10V$	50	100	—	25	75	—	V/mV
Power Consumption	P_d	$V_{OUT} = 0$	—	50	90	—	50	90	mW
Settling Time to 0.1% (Summing Node Error)	t_S	$A_V = -1$ (Notes 1, 2) $V_{IN} = 5V$	—	0.7	1.0	—	0.7	1.0	μs
Slew Rate (Notes 2, 3)	SR	$A_V = -1$, $R_S = 3k$ to $5k\Omega$	12	18	—	12	18	—	V/μs
Large-Signal Bandwidth (Notes 3, 4)			150	250	—	150	250	—	kHz
Small-Signal Bandwidth (Notes 3, 4)			1.5	2.5	—	1.5	2.5	—	MHz
Risetime	t_r	$A_V = -1$ $V_{IN} = 50mV$	—	150	—	—	150	—	ns
Overshoot	OS		—	2	—	—	2	—	%

NOTES:
1. $R_L = 25k\Omega$; $C_L = 50pF$. See Settling Time Test Circuit.
2. Sample tested.
3. See applications information.
4. Guaranteed by design.

ELECTRICAL CHARACTERISTICS at $V_S = \pm 15V$, $-55°C \leq T_A \leq +125°C$ for OP-01, OP-01G and $0°C \leq T_A \leq +70°C$ for OP-01H, OP-01C, unless otherwise noted.

			OP-01 OP-01H			OP-01G OP-01C			
PARAMETER	**SYMBOL**	**CONDITIONS**	**MIN**	**TYP**	**MAX**	**MIN**	**TYP**	**MAX**	**UNITS**
Input Offset Voltage	V_{OS}	$R_S \leq 20k\Omega$	—	0.4	1.0	—	3.0	6.0	mV
Input Offset Current	I_{OS}		—	1	4	—	4	40	nA
Input Bias Current	I_B		—	30	50	—	50	200	nA
Input Voltage Range	IVR		±10	±13	—	±10	±13	—	V
Common-Mode Rejection Ratio	CMRR	$V_{CM} = \pm 10V$ $R_S \leq 20k\Omega$	85	110	—	80	100	—	dB
Power Supply Rejection Ratio	PSRR	$V_S = \pm 5V$ to $\pm 20V$ $R_S \leq 20k\Omega$	—	10	60	—	100	150	μV/V
Large-Signal Voltage Gain	A_{VO}	$R_L \geq 2k\Omega$ $V_O = \pm 10V$	30	60	—	15	50	—	V/mV
Output Voltage Swing	V_O	$R_L \geq 5k\Omega$ $R_L \geq 2k\Omega$	±12.5 ±12.0	±13.5 ±13.0	— —	±12.5 ±12.0	±13.5 ±13.0	— —	V
Offset Voltage Drift (Note 1)	TCV_{OS}	$R_S \leq 5k\Omega$	—	2	8	—	5	20	μV/°C

NOTE:
1. Sample tested.

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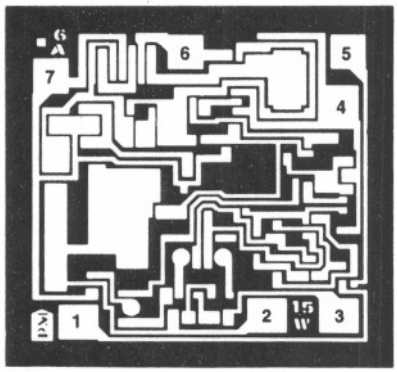
DICE CHARACTERISTICS (125°C TESTED DICE AVAILABLE)



DIE SIZE 0.047 × 0.043 inch, 2021 sq. mils
(1.19 × 1.09 mm, 1.30 sq. mm)

1. NULL
2. INVERTING INPUT
3. NONINVERTING INPUT
4. V−
5. NULL
6. OUTPUT
7. V+

WAFER TEST LIMITS at $V_S = \pm 15V$, $T_A = 25°C$ for OP-01N, OP-01G and OP-01GR devices; $T_A = 125°C$ for OP-01NT and OP-01GT devices, unless otherwise noted.

PARAMETER	SYMBOL	CONDITIONS	OP-01NT LIMIT	OP-01N LIMIT	OP-01GT LIMIT	OP-01G LIMIT	OP-01GR LIMIT	UNITS
Input Offset Voltage	V_{OS}	$R_S \leq 20k\Omega$	1.0	0.7	3.0	2.0	5.0	mV MAX
Input Offset Current	I_{OS}		4	2	10	5	20	nA MAX
Input Bias Current	I_B		50	30	100	50	100	nA MAX
Input Voltage Range	IVR		±10	±12	±10	±12	±12	V MIN
Common-Mode Rejection Ratio	CMRR	$V_{CM} = \pm 10V$ $R_S \leq 20k\Omega$	85	85	80	80	80	dB MIN
Power Supply Rejection Ratio	PSRR	$V_S = \pm 5V$ to $\pm 20V$ $R_S \leq 20k\Omega$	60	60	100	100	150	µV/V MAX
Output Voltage Swing	V_{OM}	$R_L \geq 5k\Omega$ $R_L \geq 2k\Omega$	±12.5 ±12.0	±12.5 ±12.0	±12.5 ±12.0	±12.5 ±12.0	±12.5 ±12.0	V MIN
Large-Signal Voltage Gain	A_{VO}	$R_L \geq 2k\Omega$ $V_O = \pm 10V$	30	50	25	50	25	V/mV MIN
Power Consumption	P_d	$V_{OUT} = 0$	—	90	—	90	90	mW MAX

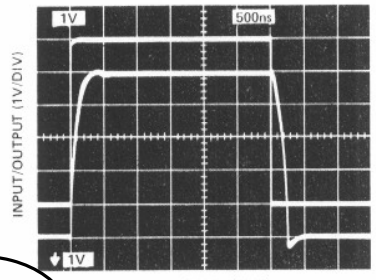
NOTES:
For 25°C characteristics of NT & GT devices, see N & G characteristics respectively.
Electrical tests are performed at wafer probe to the limits shown. Due to variations in assembly methods and normal yield loss, yield after packaging is not guaranteed for standard product dice. Consult factory to negotiate specifications based on dice lot qualification through sample lot assembly and testing.

TYPICAL ELECTRICAL CHARACTERISTICS at $V_S = \pm 15V$, $T_A = 25°C$, unless otherwise noted.

PARAMETER	SYMBOL	CONDITIONS	ALL GRADES TYPICAL	UNITS
Slew Rate	SR	$A_{VCL} = -1$, $R_S = 3k\Omega$ to $5k\Omega$	18	V/µs
Settling Time to 0.1% (Summing Node Error)	t_S	$V_{IN} = 5V$ $A_V = -1$ $R_L = 2k\Omega$ (See Settling Time Test Circuit) $C_L = 50pF$	1.0	µs
Large-Signal Bandwidth			250	kHz
Small-Signal Bandwidth			2.5	MHz
Risetime	t_r	$V_{IN} = 50mV$ $A_V = -1$	150	ns

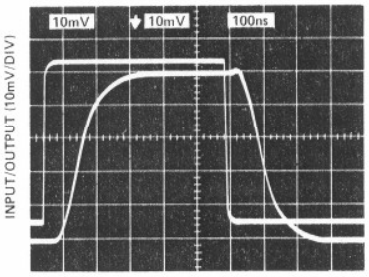
TYPICAL PERFORMANCE CHARACTERISTICS

LARGE-SIGNAL PULSE RESPONSE



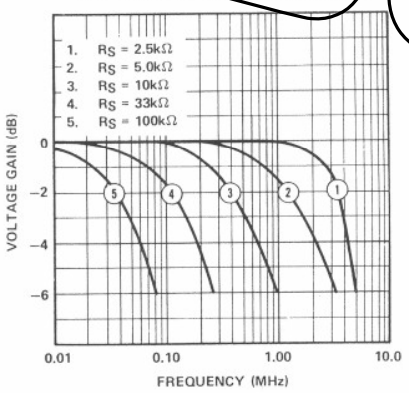
$V_S = \pm 15V$, $A_V = -1$, $R_L = 2k\Omega$, $C_L = 50pF$

SMALL-SIGNAL PULSE RESPONSE

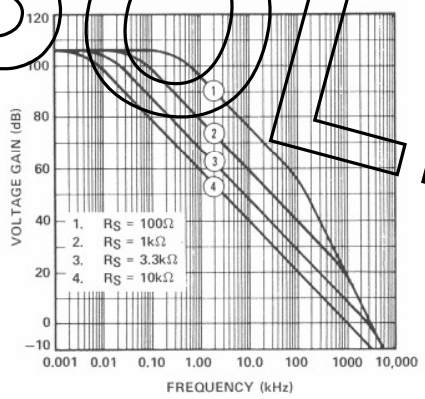


$V_S = \pm 15V$, $A_V = -1$, $R_L = 2k\Omega$, $C_L = 50pF$

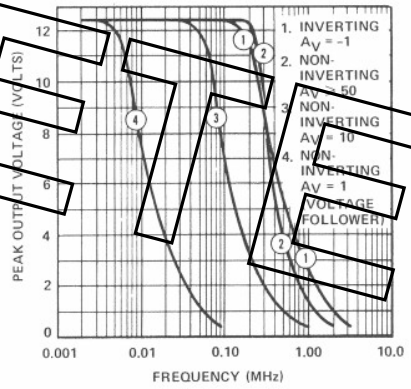
UNITY-GAIN BANDWIDTH vs SOURCE RESISTANCE



OPEN-LOOP GAIN vs FREQUENCY



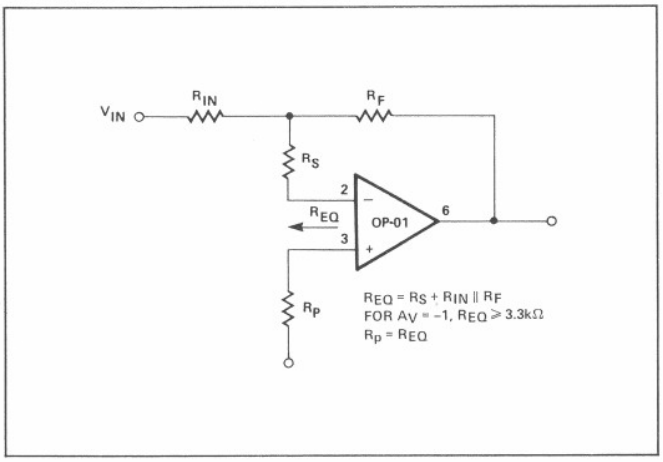
LARGE-SIGNAL OUTPUT SWING vs FREQUENCY



APPLICATIONS INFORMATION

The OP-01 incorporates an internal feed-forward compensation network to provide fast slewing and settling times in all inverting and moderate-to-high-gain noninverting applications. Unity-gain bandwidth is a function of the total equivalent source resistance seen by the inverting terminal. Proper choice of this resistance will allow the user to maxmize bandwidth while assuring proper stability. The equivalent-inverting-terminal-resistance is defined as $R_{IN} \| R_F$, and it must be greater than 3.3kΩ to assure stability in all closed-loop gain configurations including unity gain. Should $R_{IN} \| R_F \leq 3.3k\Omega$, a resistor ($R_S$) may be placed between the inverting input and the sum node to provide the required resistance. (See Fast Inverting Amplifier Diagram.) Lower values of total equivalent resistance may be used to improve bandwidth in higher closed-loop gain configurations, as indicated by the Open-Loop Gain vs. Frequency plot.

FAST INVERTING AMPLIFIER



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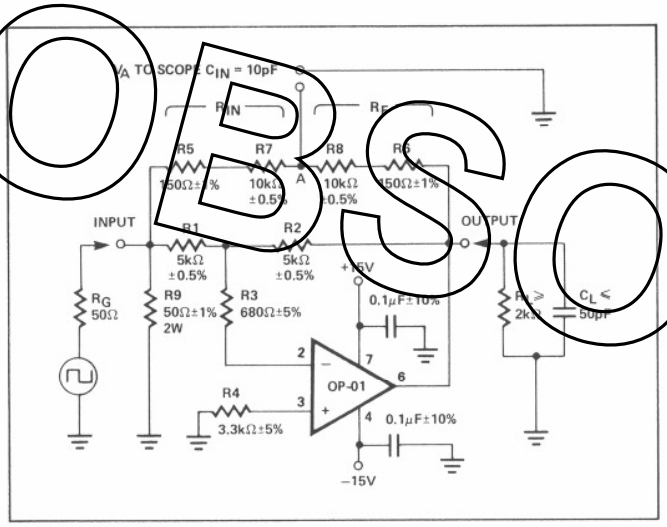
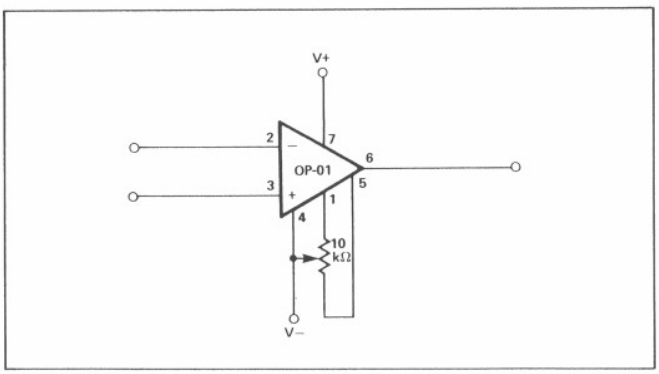
SETTLING-TIME TEST CIRCUIT

Settling time may be measured using the circuit shown below. This circuit incorporates the "false sum node" technique to produce accurate, repeatable results. For a 5V input step, 0.1% settling will be achieved when the false sum node settles to within ±2.5mV of its final value. The oscilloscope used for observation of the false sum node should have wide bandwidth, fast overload recovery time, and be used with a low capacity probe (≤ 10pF, including strays). A Tektronix 7504 scope with a 7A11 probe or equivalent is suggested. The pulse generator should have a 50Ω output impedance and be capable of a 5V rise time in ≤ 20ns with ringing less than 2.5mV after 0.5μs. Measurements to 0.1% require R_{IN} to equal R_F within 0.01%; R_5 and R_6 are used as trimming resistors to achieve this matching.

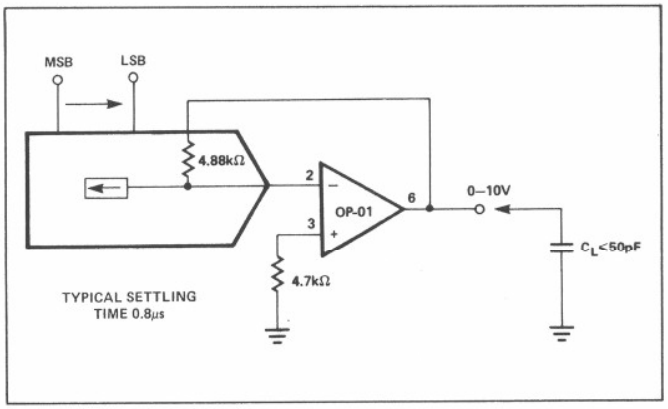


OFFSET NULLING CIRCUIT



TYPICAL APPLICATIONS

FAST VOLTAGE-OUTPUT D/A CONVERTER



PRECISION POWER-BOOSTER CIRCUIT